Dual N-Channel Enhancement Mode MOSFET

GBLN6603-S8

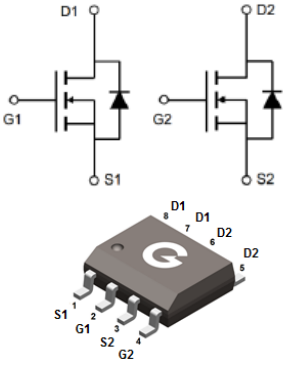
Features

- Advanced shielded-gate trench technology
- Super low gate charge
- Low on-resistance
- Excellent C_{dV} / d_t effect decline
- RoHS compliant with Halogen-free

HF

Mechanical Data

- Case: SOP-8
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



SOP-8

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
GBLN6603-S8	SOP-8	4000 pcs / Tape & Reel	GBLN6603

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	60	V
Gate-to-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current (T_C = 25°C)	I_D	14	A
Continuous Drain Current (T_A = 25°C) *1		7.5	A
Continuous Drain Current (T_A = 100°C) *1		5.3	A
Pulsed Drain Current (t_p =10μs, T_A = 25°C)	I_{DM}	75	A
Single Pulse Avalanche Energy *3	E_{AS}	20	mJ
Power Dissipation (T_C = 25°C)	P_D	7.5	W
Power Dissipation (T_A = 25°C) *1		2.2	W
Operating Junction Temperature Range	T_J	-55 ~ +175	°C
Storage Temperature Range	T_{STG}	-55 ~ +175	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	-	20	°C/W
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	-	63	70	°C/W

Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 48V, V_{GS} = 0V	-	-	1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
On Characteristics						
$R_{DS(ON)}$	Drain-Source On-resistance *2	V_{GS} = 10V, I_D = 10A	-	15	20	mΩ
		V_{GS} = 4.5V, I_D = 10A	-	20	28	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1	1.8	2.5	V
R_G	Gate Resistance	V_{GS} = 0V, f = 1MHz	-	2.6	-	Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	V_{GS} = 0V V_{DS} = 30V f = 1.0MHz	-	677	-	pF
C_{OSS}	Output Capacitance		-	160	-	
C_{RSS}	Reverse Transfer Capacitance		-	7	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time	V_{DD} = 30V V_{GS} = 15V I_D = 10A R_G = 3.3Ω	-	7	-	ns
t_r	Turn-on Rise Time		-	35	-	
$t_{d(OFF)}$	Turn-Off Delay Time		-	22	-	
t_f	Turn-Off Fall Time		-	24	-	
Q_G	Total Gate-Charge	V_{DD} = 30V V_{GS} = 10V I_D = 10A	-	12.7	-	nC
Q_{GS}	Gate to Source Charge		-	1.8	-	
Q_{GD}	Gate to Drain (Miller) Charge		-	3.2	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage *2	I_{SD} = 10A, V_{GS} = 0V	-	0.9	1.2	V
trr	Reverse Recovery Time	I_F = 10A, V_{GS} = 0V d_I/d_t = 100A/μs	-	26	-	ns
Qrr	Reverse Recovery Charge		-	15	-	nC

Notes:

1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper
2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%
3. The E_{AS} data shows Max. rating. The test condition is V_{DD} = 25V, V_{GS} = 10V, L = 0.1mH

Ratings and Characteristics Curves (@ T_A = 25°C unless otherwise specified)

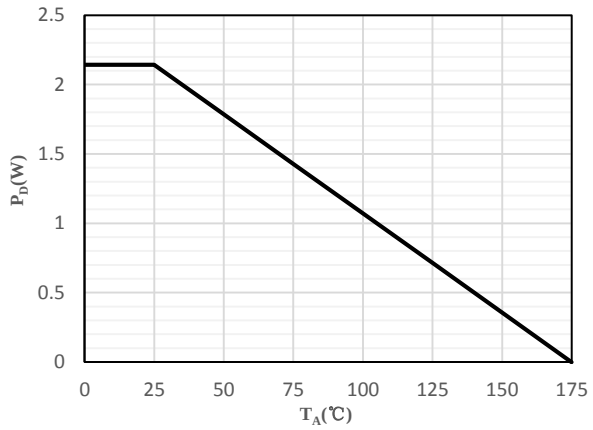


Fig 1 Power Dissipation

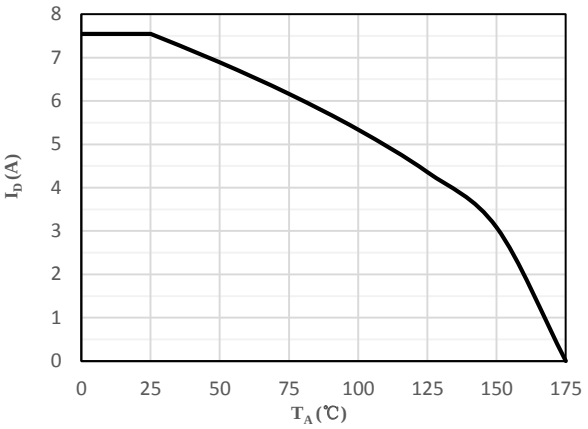


Fig 2 Drain Current

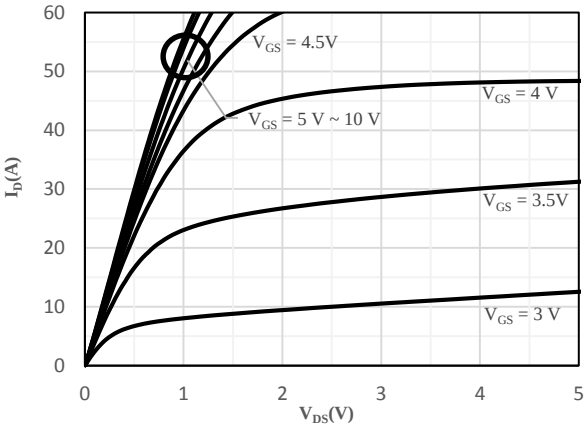


Fig 3 Typical Output Characteristics

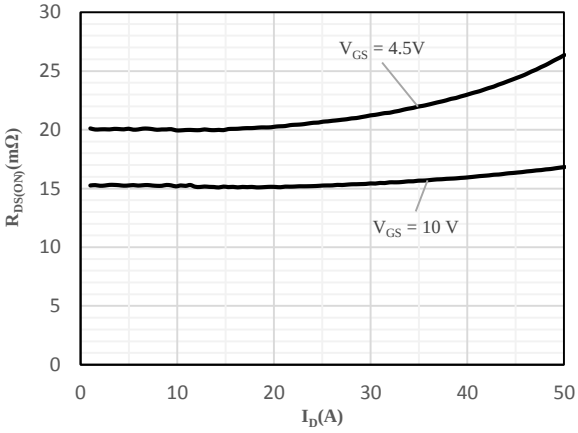


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

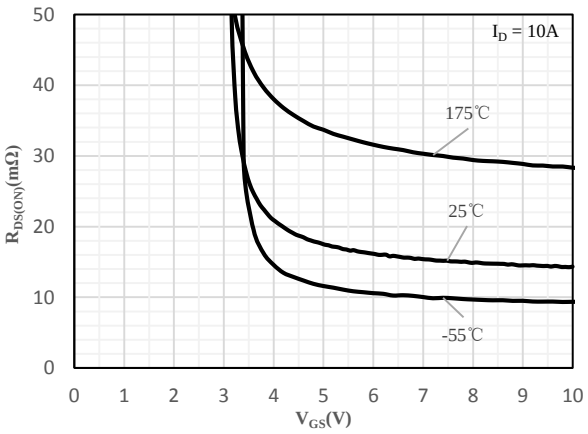


Fig 5 On-Resistance vs. Gate-Source Voltage

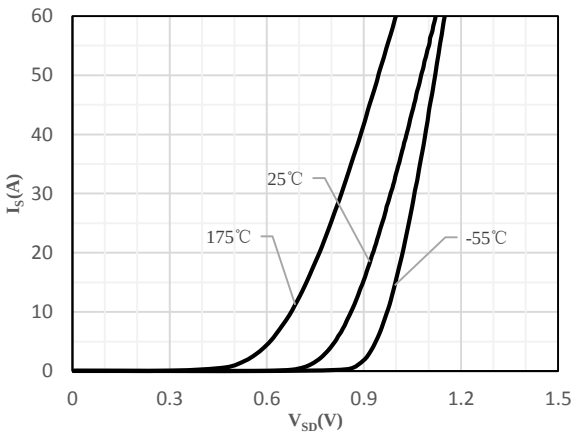


Fig 6 Body-Diode Characteristics

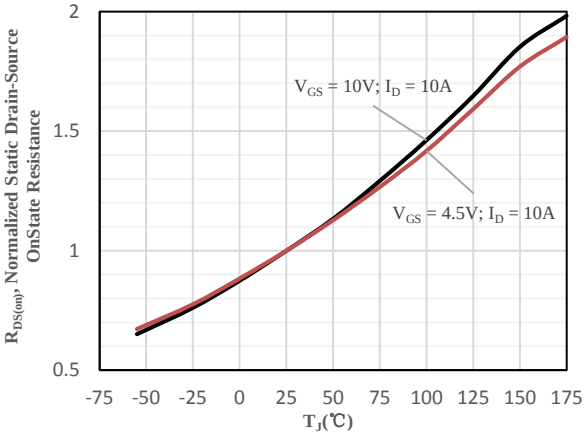


Fig 7 Normalized On-Resistance vs. Junction Temperature

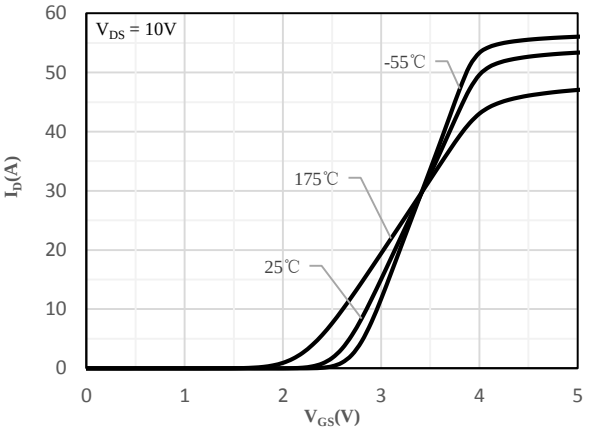


Fig 8 Transfer Characteristics

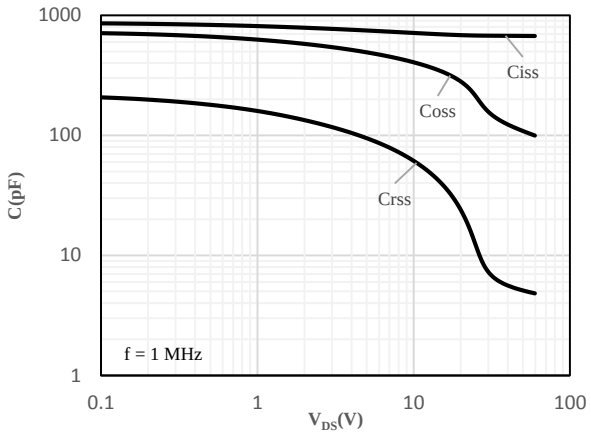


Fig 9 Capacitance Characteristics

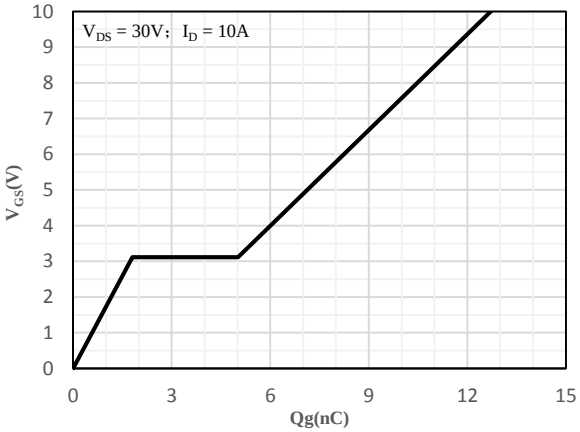


Fig 10 Gate-Charge Characteristics

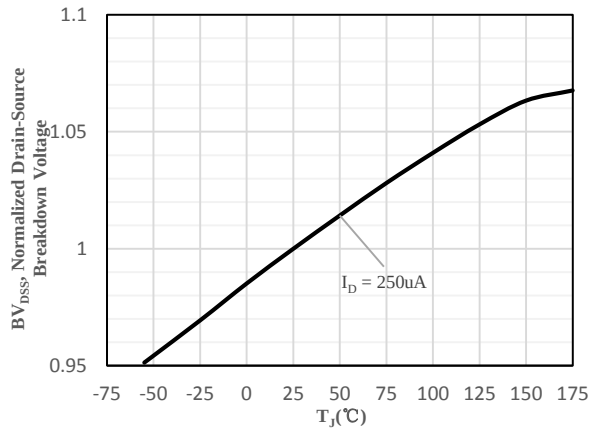


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

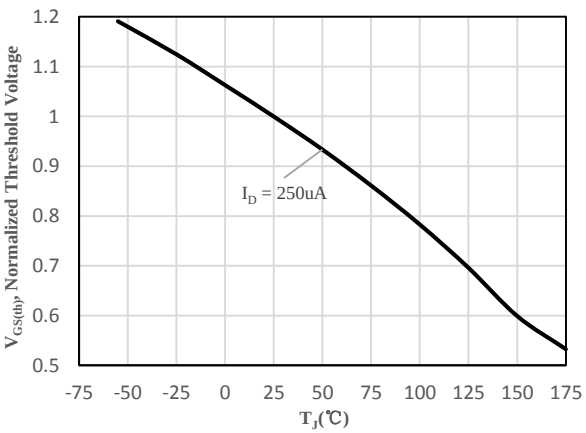


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

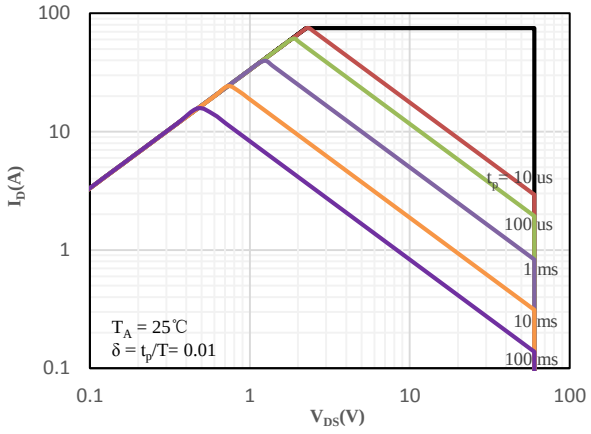


Fig 13 Safe Operating Area

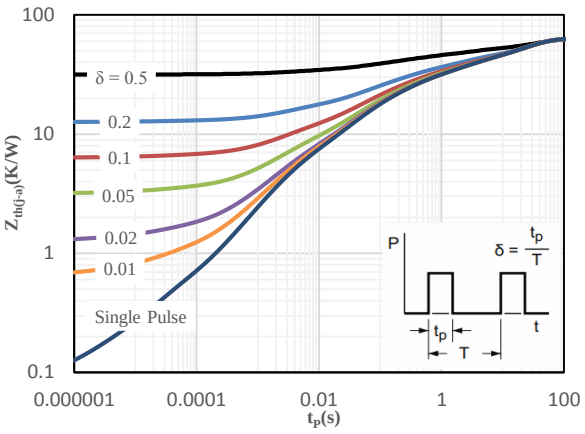
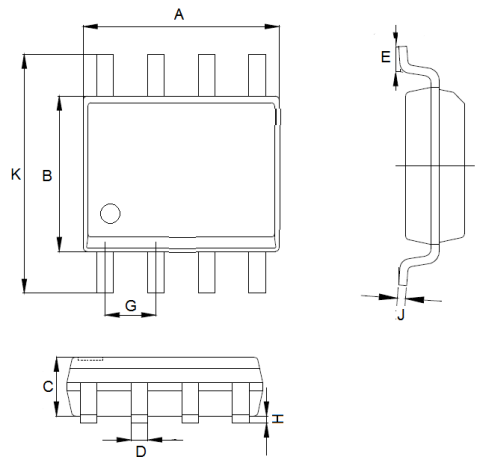


Fig 14 Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)



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Dimension	**Min.**	**Max.**
A	4.80	5.20
B	3.80	4.20
C	1.30	1.50
D	0.30	0.50
E	0.40	1.00
G	1.17	1.37
H	0.10	0.30
J	0.10	0.30
K	5.80	6.20

Mounting Pad Layout (Unit: mm)

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